NSN 5961-00-181-0660

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-181-0660 **Inclosure Material:** Glass **Overall Length:** Between 0.140 inches and 0.205 inches **Terminal Length:** Between 0.600 inches and 1.500 inches **Overall Diameter:** Between 0.060 inches and 0.110 inches **Mounting Method:** Terminal **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 working peak reverse voltage **Current Rating Per Characteristic:** 1.00 amperes average on-state current, 180 degrees conduction angle, average over a full 60-hz cycle and 30.00 amperes peak forward surge current **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-prf-19500/228 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0

Mil-prf-19500 spec.

Mil-std (military Standard):